SM Technology Co.，Limited

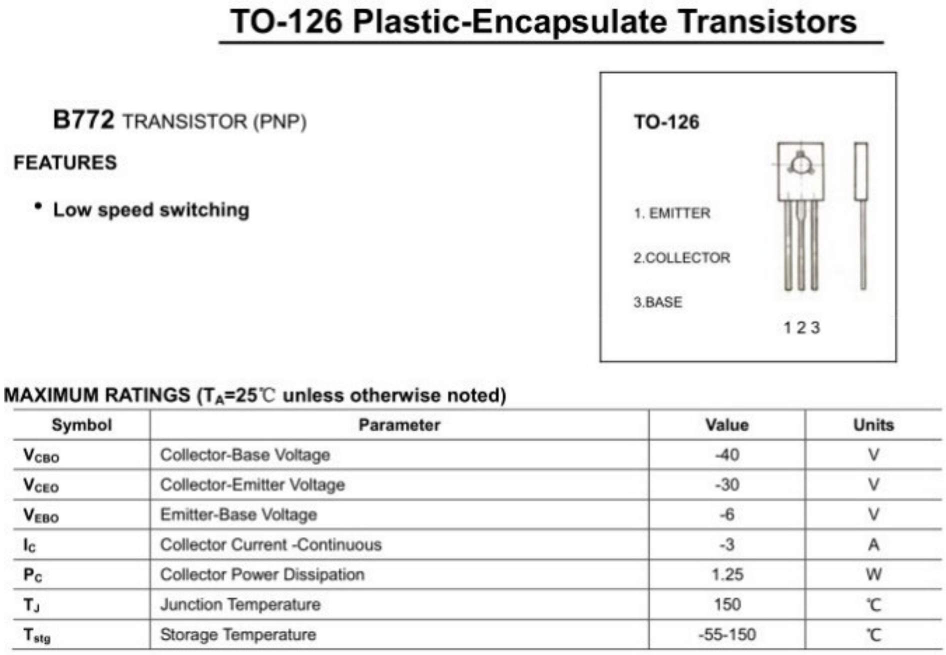
TO-126 Bipolar Transistor B772

Specifications

TO-126 Bipolar Transistor B772

1) Low Collector-Emitter Saturation Voltage & Large Collector Current

2) High Power Dissipation



TO-126 Plastic-Encapsulate Transistors

B772 TRANSISTOR (PNP)

FEATURES

- **Low speed switching**

TO-126

1. EMITTER
2. COLLECTOR
3. BASE

1 2 3

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current -Continuous	-3	A
P_C	Collector Power Dissipation	1.25	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃